

**AMENDMENTS TO THE SPECIFICATION:**

*Please amend the paragraph beginning at page 4, line 17, as follows:*

For the film formation, gases containing the starting materials are introduced through the gas introduction ports 105 and 106 into a space between the ceiling plate 102 and the upper ends of the partition plates 104 and mixed together. The resulting mixed gas G is ~~blown~~ discharged downward along the partition plates 104 and supplied to the surface of the silicon substrate 21 that travels below the assembly 101 while being conveyed by a conveyor belt 23. This gas G decomposes on the surface of the silicon substrate 21 and forms a film having a composition that corresponds to the kinds of the starting materials on the surface of the silicon substrate 21. The remaining gas is exhausted ~~discharged~~ from an exhaust port 110 to the outside through a gap 109 between the assembly 101 and a cover protuberance 108.

*Please amend the paragraph beginning at page 16, line 7, as follows:*

In the apparatus shown in Fig. 3, the silicon substrate 1 is first pre-heated by a pre-heater 2 and conveyed by a conveyor belt 3 to a film formation position 13. In the film formation position 13, a heater 4 sets the film formation temperature. The titanium compound and the compound of the dopant element, both in a gaseous state, are passed through gas lines 7 and 8, respectively, and supplied to the surface of the silicon substrate 1 from a dispersion head 5. The titanium compound and the compound of the dopant element thus supplied are thermally decomposed on the surface of the silicon substrate 1, forming a titanium oxide film. In the apparatus shown in Fig. 3, the conveyor belt 3 conveys the silicon substrate 1 from the position immediately below the discharge port of the gas line 7 of the dispersion head 5 for the compound of the dopant element, through the position immediately below the discharge port of the gas line

8 for the titanium compound to the position immediately below the discharge port for the atmospheric gas of the gas line 9.

*Please amend the paragraph beginning at page 17, line 6, as follows:*

In the film formation position ~~portion~~ 13, exhaust gas that comprises the carrier gas, the dilution gas, the undecomposed starting materials and the decomposition product ~~products~~ is exhausted ~~discharged~~ from both sides of the dispersion head 5 to an exhaust port 12.